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<u>Texas Instruments</u> <u>SN74LVC2G125DCTR</u>

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Datasheet of SN74LVC2G125DCTR - IC BUS BUFF TRI-ST DL N-INV SM8

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SN74LVC2G125

SCES204P - APRIL 1999 - REVISED JANUARY 2016

SN74LVC2G125 Dual Bus Buffer Gate With 3-State Outputs

1 Features

- Available in the Texas Instruments NanoFree[™] Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.3 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Max of 5.5 V Down to the V_{CC} Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model
 - 200-V Machine Model
 - 1000-V Charged-Device Model

2 Applications

- Cable Modem Termination Systems
- High-Speed Data Acquisition and Generation
- · Military: Radars and Sonars
- Motor Controls: High-Voltage
- Power Line Communication Modems
- SSDs: Internal or External
- Video Broadcasting and Infrastructure: Scalable Platforms
- Video Broadcasting: IP-Based Multi-Format Transcoders
- Video Communications Systems

3 Description

The SN74LVC2G125 device is a dual bus buffer gate, designed for 1.65-V to 5.5-V V_{CC} operation. This device features dual line drivers with 3-state outputs. The outputs <u>are</u> disabled when the associated output-enable (\overline{OE}) input is high.

NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver

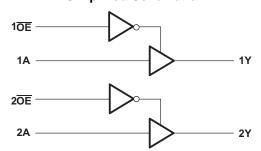
This device is fully specified for partial-power-down applications using $I_{\rm off}$. The $I_{\rm off}$ circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE
	SM8 (8)	2.95 mm × 2.80 mm
SN74LVC2G125	US8 (8)	2.30 mm × 2.00 mm
	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic





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Char	Revision History nges from Revision O (January 2015) to Revision P			Page
	added overbar for active low to $1\overline{OE}$ and $2\overline{OE}$ to the Simplification of the Absolute Maximum Re			
	added T _J Junction temperature to the <i>Absolute Maximum Ra</i> added overbar for active low to 1 0E and 2 0E to the <i>Function</i>			
Char A 7 s	nges from Revision N (November 2013) to Revision O Added Applications, Device Information table, Pin Functions Typical Characteristics, Feature Description section, Device a ection, Power Supply Recommendations section, Layout se Mechanical, Packaging, and Orderable Information section	table, <i>E Function</i>	SD Ratings table, Thermal Information table, nal Modes, Application and Implementation levice and Documentation Support section, and	Page
Char	nges from Revision M (January 2007) to Revision N			Page
ι	Updated document to new TI data sheet format			1
R	Removed Ordering Information table			1
L	lpdated Features			1
C	changed MAX operating temperature to 125°C in Recomme	nded O _l	perating Conditions table	5

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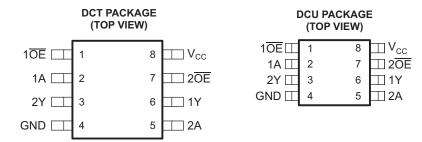


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5 Pin Configuration and Functions



See mechanical drawings for dimensions.



See mechanical drawings for dimensions.

Pin Functions

P	PIN		PIN					
NAME	DCT, DCU, YZP	TYPE	DESCRIPTION					
1A	2	I	Input					
2A	5	I	Input					
1 OE	1	I	Output Enable for buffer 1					
2 OE	7	I	Output Enable for buffer 2					
1Y	6	0	Output					
2Y	3	0	Output					
GND	4	_	Ground					
V _{CC}	8	_	Power pin					



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6 Specifications

6.1 Absolute Maximum Ratings

See⁽¹⁾

				MIN	MAX	UNIT
V_{CC}	Supply voltage range				6.5	V
VI	Input voltage range (2)			-0.5	6.5	V
Vo	O Voltage range applied to any output in the high-impedance or power-off state (2)				6.5	V
Vo	O Voltage range applied to any output in the high or low state (2)(3)			-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0			-50	mA
I _{OK}	Output clamp current	V _O < 0			-50	mA
Io	Continuous output current	·			±50	mA
	Continuous current through V _{CC} or GND				±100	mA
T _{stg}	g Storage temperature range			-65	150	ç
TJ	Junction temperature				150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

PARAMETER	PARAMETER DEFINITION				
Flactroatatio	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	2000			
V _(ESD) Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	1000	V		

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⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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6.3 Recommended Operating Conditions

over recommended operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT					
.,	0 1 1	Operating	1.65	5.5						
V_{CC}	Supply voltage	Data retention only	1.5		V					
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}							
.,	18.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.	V _{CC} = 2.3 V to 2.7 V	1.7							
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V					
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}							
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}						
.,	Laurent Sancture Norma	V _{CC} = 2.3 V to 2.7 V		0.7						
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V					
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}						
VI	Input voltage	·	0	5.5	V					
.,	Output walte wa	High or low state	0	V_{CC}	· V					
Vo	O Output voltage	3-state		5.5	V					
		V _{CC} = 1.65 V		-4						
		V _{CC} = 2.3 V		-8						
I _{OH}	High-level output current			-16	mA					
		V _{CC} = 3 V		-24						
		V _{CC} = 4.5 V		-32						
		V _{CC} = 1.65 V		4						
		V _{CC} = 2.3 V		8						
I _{OL}	Low-level output current			16	mA					
		V _{CC} = 3 V		24						
		V _{CC} = 4.5 V		32						
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20						
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V					
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5						
T _A	Operating free-air temperature		-40	125	°C					

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		DCT	DCU	YZP	UNIT
	THERMAL METRIC"		8 PINS	8 PINS	UNII
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

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6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETER	TEST CONDITIONS		-40°(C to 85°C	-40°	-40°C to 125°C			
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾ MA	X MIN	TYP ⁽¹⁾ N	MAX		
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1		V _{CC} - 0.1				
	I _{OH} = -4 mA	1.65 V	1.2		1.2				
	J. 0 A	1.8 V	1.4						
V_{OH}	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9			V	
	I _{OH} = -16 mA	3 V	2.4		2.4				
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8				
	I _{OL} = 100 μA	1.65 V to 5.5 V		C	.1		0.1		
	I _{OL} = 4 mA	1.65 V		0.	15	().45		
	I = 9 m A	1.8 V		0.	15			V	
V_{OL}	$I_{OL} = 8 \text{ mA}$	2.3 V		C	.3		0.3		
	I _{OL} = 16 mA	3 V		C	.4		0.4		
	I _{OL} = 24 mA	3 V		0.	55	().55		
	I _{OL} = 32 mA	4.5 V		0.	55	().75		
I _I A or $\overline{\text{OE}}$ inputs	V _I = 5.5 V or GND	0 to 5.5 V		:	±5		±5	μΑ	
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±	10		±10	μΑ	
I_{OZ}	V _O = 0 to 5.5 V	3.6 V			10		10	μΑ	
I _{CC}	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V			10		10	μΑ	
ΔI_{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V		5	00		500	μΑ	
C _i Data inputs	$V_{I} = V_{CC}$ or GND	3.3 V		3.5		3.5		pF	
Control inputs	AI - ACC OL CLAD	3.3 V		4		4		ρı	
C _o	$V_O = V_{CC}$ or GND	3.3 V		6.5		6.5		pF	

⁽¹⁾ All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

						-40°C t	o 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2		V _{CC} = 3 ± 0.3		V _{CC} = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Y	3.3	9.1	1.5	4.8	1.4	4.3	1	3.7	ns
t _{en}	ŌĒ	Y	4	9.9	1.9	5.6	1.2	4.7	1.2	3.8	ns
t _{dis}	ŌĒ	Υ	1.5	11.6	1	5.8	1.4	4.6	1	3.4	ns

6.7 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

		−40°C to 125°C									
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.15		V _{CC} = 2 ± 0.2	2.5 V ! V	V _{CC} = 3 ± 0.3	3.3 V 5 V	V _{CC} = ± 0.5	5 V V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Υ	3.3	10.1	1.5	5.8	1.4	5.3	1	4.2	ns
t _{en}	ŌĒ	Y	4	10.9	1.9	6.6	1.2	5.7	1.2	4.3	ns
t _{dis}	ŌĒ	Υ	1.5	12.6	1	6.8	1.4	5.6	1	3.9	ns

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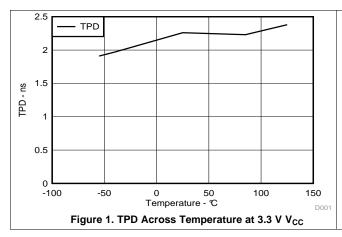
6.8 Operating Characteristics

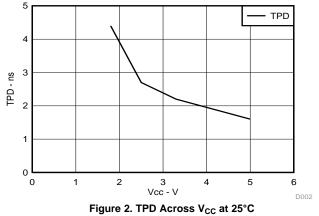
 $T_A = 25^{\circ}$

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	PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
	PARAIVIETER	`	CONDITIONS	TYP	TYP	TYP	TYP	UNII	
_	Power dissipation Outputs enabled		f 40 MH-	19	19	20	22	~F	
C_{pd}	capacitance	Outputs disabled	f = 10 MHz	2	2	2	3	pF	

6.9 Typical Characteristics





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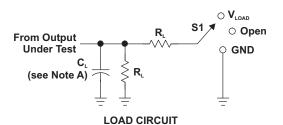


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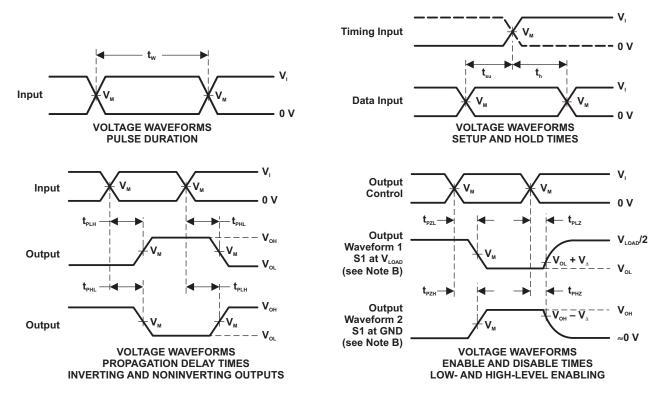
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Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

.,,	INI	PUTS	.,	.,			.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C ^r	R _∟	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C. includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $\dot{t}_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

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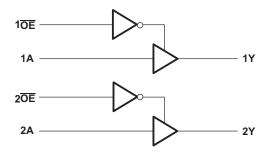
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8 Detailed Description

8.1 Overview

The SN74LVC2G125 device contains dual buffer gate device with output enable control and performs the Boolean function Y = A. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

- Wide operating voltage range
 - Operates from 1.65 V to 5.5 V
- Allows down voltage translation
- Inputs accept voltages to 5.5 V
- I_{off} Feature
 - Allows voltages on the inputs and outputs, when V_{CC} is 0 V

8.4 Device Functional Modes

Table 1. Function Table

INP	UTS	OUTPUT
ŌĒ	Α	Y
L	Н	Н
L	L	L
Н	X	Z

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Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G125 device is a high drive CMOS device that can be used as a output enabled buffer with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to V_{CC}.

9.2 Typical Application

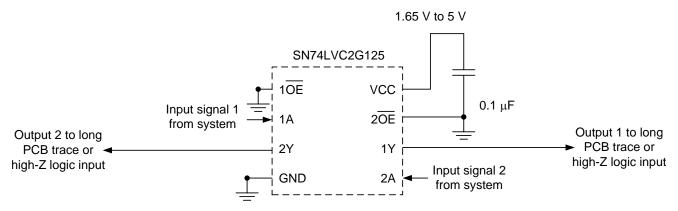


Figure 4. Typical Application Schematic

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions:
 - For rise time and fall time specifications, see (Δt/ΔV) in the Recommended Operating Conditions table.
 - For specified high and low levels, see (V_{IH} and V_{II}) in the *Recommended Operating Conditions* table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating Conditions table at any valid V_{CC}.
- 2. Recommend Output Conditions:
 - Load currents should not exceed (Io max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.

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Outputs should not be pulled above V_{CC} .

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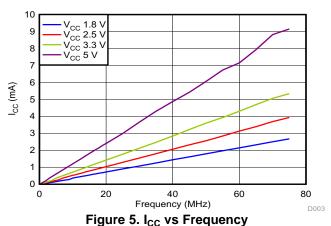
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Typical Application (continued)

9.2.3 Application Curves



10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a 0.1- μ F capacitor is recommended and if there are multiple V_{CC} pins then a 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 6 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} , whichever makes more sense or is more convenient.

11.2 Layout Example

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Figure 6. Layout Diagram



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12 Device and Documentation Support

12.1 Trademarks

NanoFree is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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PACKAGE OPTION ADDENDUM

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PACKAGING INFORMATION

Orderskie Berries	Ctatura	Daalaana Tuma	Daalisas	Dina	Daalaaaa	Faa Dlan	Lead/Dall Finish	MCI Deal Terre	On Tame (90)	Davies Maulius	Commiss
Orderable Device	Status (1)	Package Type	Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC2G125DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
74LVC2G125DCTRE6	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU SNBI	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
74LVC2G125DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
74LVC2G125DCURE4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
74LVC2G125DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
74LVC2G125DCUTE4	ACTIVE	VSSOP	DCU	8		TBD	Call TI	Call TI	-40 to 125		Samples
74LVC2G125DCUTG4	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25R	Samples
SN74LVC2G125DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C25 Z	Samples
SN74LVC2G125DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(25 ~ C25Q ~ C25R) CZ	Samples
SN74LVC2G125DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 125	(C25Q ~ C25R)	Samples
SN74LVC2G125YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	(CM2 ~ CM7 ~ CMN)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

Pb-Free (RoHS): Ti's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Addendum-Page 1

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.



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PACKAGE OPTION ADDENDUM

www.ti.com 22-Jan-2016

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G125:

Automotive: SN74LVC2G125-Q1

NOTE: Qualified Version Definitions:

Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

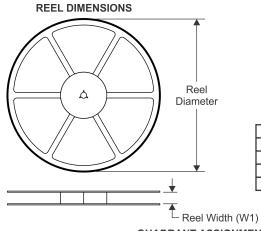
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PACKAGE MATERIALS INFORMATION

www.ti.com 1-Feb-2016

TAPE AND REEL INFORMATION

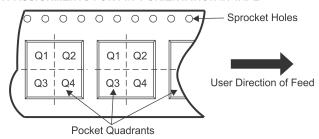


TAPE DIMENSIONS + K0 + P1 + B0 W Cavity - A0 +

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape

th (\M1)

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



P1 Pitch between successive cavity centers

*All dimensions are nominal

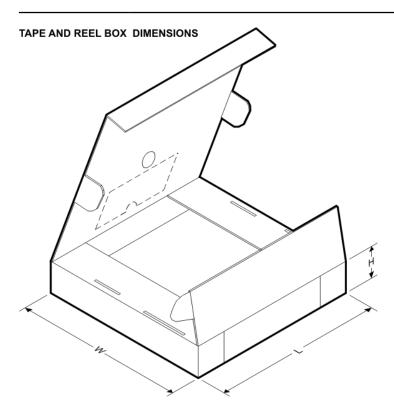
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G125DCTRE6	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
74LVC2G125DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
74LVC2G125DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G125DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G125DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
SN74LVC2G125YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

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PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

7 til dilliciono are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G125DCTRE6	SM8	DCT	8	3000	182.0	182.0	20.0
74LVC2G125DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
74LVC2G125DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G125DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G125DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC2G125YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

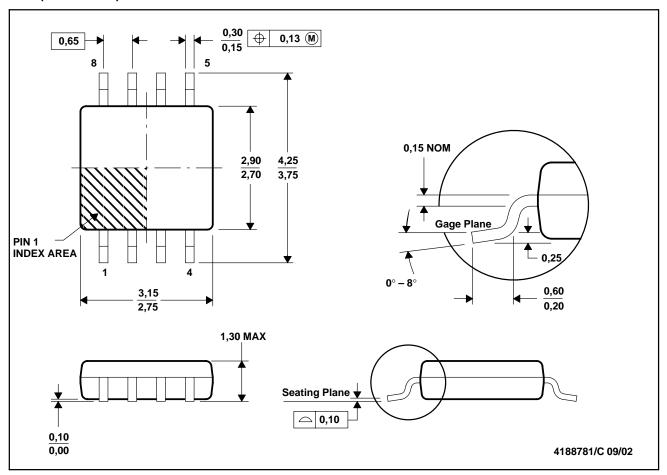
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MECHANICAL DATA

MPDS049B - MAY 1999 - REVISED OCTOBER 2002

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

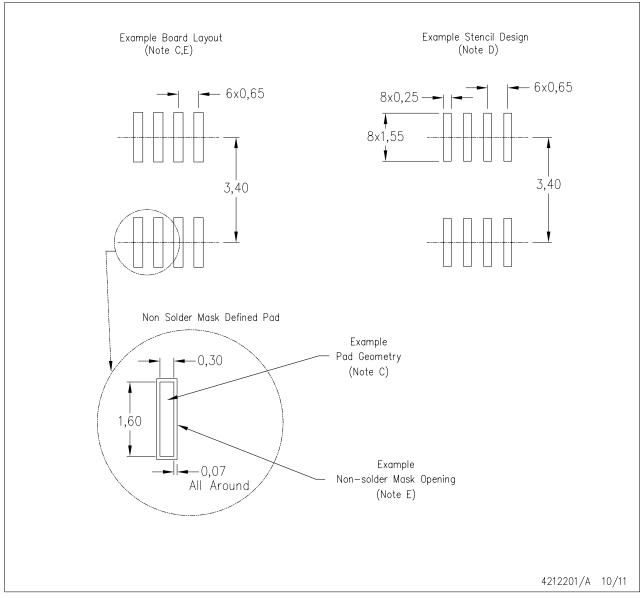




LAND PATTERN DATA

DCT (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

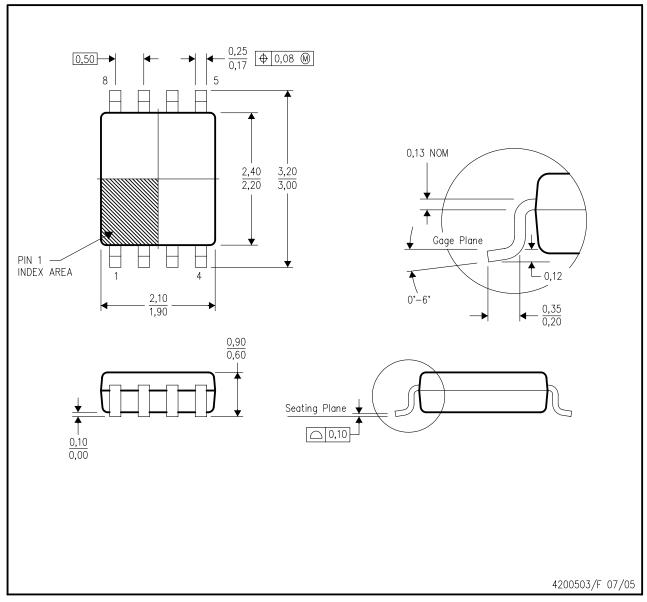
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





MECHANICAL DATA

DCU (R-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-187 variation CA.

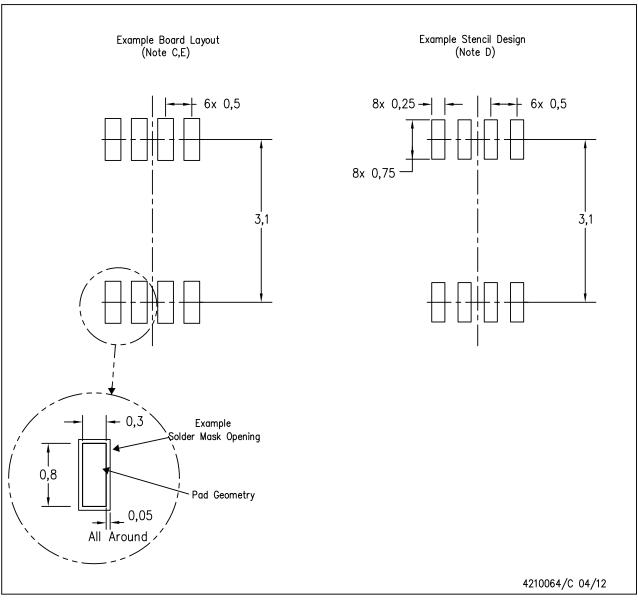




LAND PATTERN DATA

DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

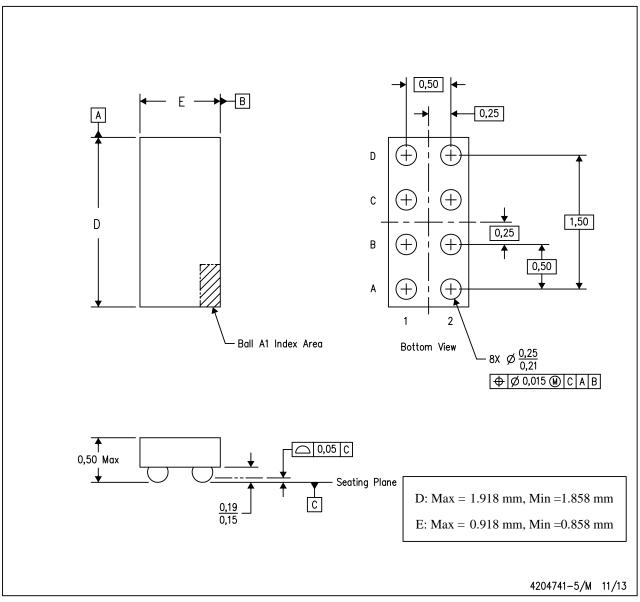




MECHANICAL DATA

YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. NanoFree™ package configuration.

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